Dr. Jean Decobert

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Jean Decobert is Epitaxy Team Leader at III-V Lab, the joint Lab of Nokia Bell Labs, Thales Research and Technology and CEA-Leti, in France. He supervises III-V semiconductor material growth (MOVPE and GSMBE) for opto- and micro-electronic applications.

He has been working on III-V epitaxial growth by MOVPE since 1987. He received his Ph. D. degree in microelectronics from Lille University and joined the National Telecommunications Research Center (CNET), France Telecom, in 1993, where he started working on the design of showerhead MOVPE reactors for InP-based HEMTs and OEIC applications.

In 1999, he joined Alcatel where he worked on SWIR and Avalanche Photodiodes. In 2004, within the III-V Lab, he started to work on growth and fabrication of advanced Electro-absorption Modulator-Lasers (EML) by Selective Area Growth (SAG), the integration platform technique for Photonic Integrated Circuits (PIC). In 2014, with CEA-Leti, he focussed on Photovoltaic III-V/Si tandem solar cells, with advanced research on GaAs and InP based tunnel junctions.

His current research interests are III-V integration on silicon, exploring different approaches such as wafer bonding, micro-transfer printing and, above all, heteroepitaxy on InPoSi wafers.